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(54) **MEMORY DEVICE**

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ABSTRACT

A memory device of embodiments includes a memory cell including: a first conductive layer; a second conductive layer; a third conductive layer provided between the first conductive layer and the second conductive layer; a variable resistance layer provided between the first conductive layer and the third conductive layer; and a switching layer provided between the third conductive layer and the second conductive layer. The switching layer contains antimony (Sb), a second element, and an oxide of a first element. The first element is at least one element selected from a group consisting of zirconium (Zr), hafnium (Hf), yttrium (Y), tantalum (Ta), lanthanum (La), cerium (Ce), magnesium (Mg), and titanium (Ti). The second element is at least one element selected from a group consisting of aluminum (Al), zinc (Zn), and gallium (Ga).

